

SILICON POWER RECTIFIER

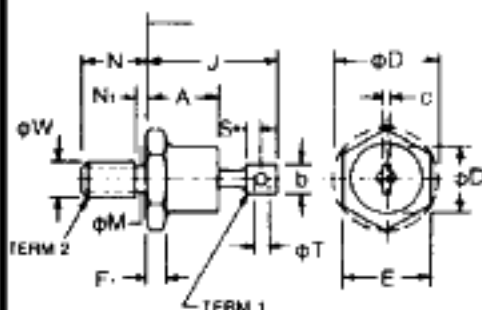
DESCRIPTION:

The **ASI 1N253** is Designed for General Purpose Power Supply Applications.

MAXIMUM RATINGS

I_o	1.0 A @ $T_c = 135\text{ }^\circ\text{C}$
V_{RWM}	100 V
T_J	$-65\text{ }^\circ\text{C}$ to $+170\text{ }^\circ\text{C}$
T_{STG}	$-65\text{ }^\circ\text{C}$ to $+175\text{ }^\circ\text{C}$
θ_{JC}	$35\text{ }^\circ\text{C/W}$

PACKAGE STYLE DO-4				
SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A		0.405		10.28
b		0.250		6.35
c				
ϕD		0.505		12.82
ϕD_1	0.265	0.424	6.74	10.76
E	0.423	0.438	10.75	11.12
F_1	0.075	0.175	1.91	4.44
J	0.600	0.800	15.24	20.32
ϕM	0.163	0.189	4.15	4.80
N	0.422	0.453	10.72	11.50
N_1		0.078		1.98
S				
ϕT	0.080	0.095	1.53	2.41
ϕW	10-32	UNF-2A	10-32	UNF-2A



CHARACTERISTICS $T_J = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIM	UNITS
I_R	$V_R = 100\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$		10 100	100 1000	μA
V_F	$I_F = 1.0\text{ A}$			1.2	V
I_{FSM}	NON REPETITIVE $t_p = 8.3\text{ mS}$	15			A

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